

XPT IGBT

$$V_{CES} = 1200V$$

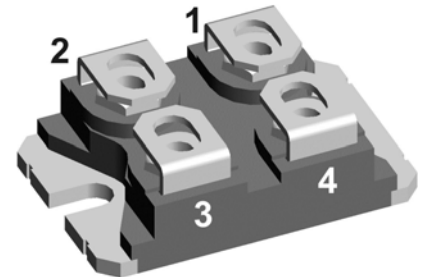
$$I_{C25} = 88A$$

$$V_{CE(sat)} = 1.8V$$

Copack

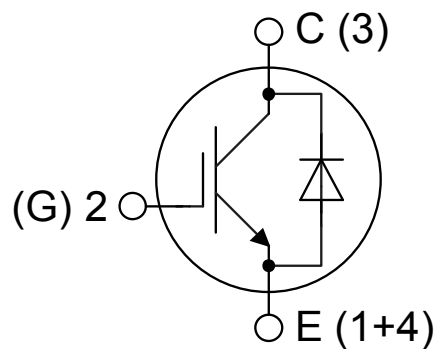
Part number

IXA60IF1200NA



Backside: collector

 E72873



Features / Advantages:

- Easy paralleling due to the positive temperature coefficient of the on-state voltage
- Rugged XPT design (Xtreme light Punch Through) results in:
 - short circuit rated for 10 μ sec.
 - very low gate charge
 - low EMI
 - square RBSOA @ 3x I_C
- Thin wafer technology combined with the XPT design results in a competitive low $V_{CE(sat)}$
- SONIC™ diode
 - fast and soft reverse recovery
 - low operating forward voltage

Applications:

- AC motor drives
- Solar inverter
- Medical equipment
- Uninterruptible power supply
- Air-conditioning systems
- Welding equipment
- Switched-mode and resonant-mode power supplies
- Inductive heating, cookers
- Pumps, Fans

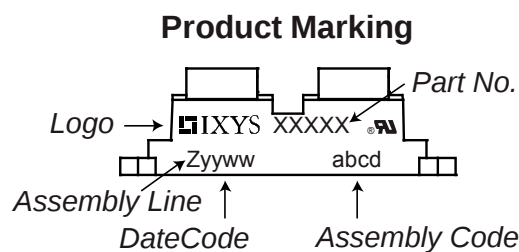
Package: SOT-227B (minibloc)

- Isolation Voltage: 3000 V~
- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Base plate: Copper internally DCB isolated
- Advanced power cycling
- Either emitter terminal can be used as main or Kelvin emitter (3 + 4)

IGBT				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V _{CES}	collector emitter voltage	T _{VJ} = 25°C				1200	V
V _{GES}	max. DC gate voltage					±20	V
V _{GEM}	max. transient gate emitter voltage					±30	V
I _{C25}	collector current	T _C = 25°C				88	A
I _{C80}		T _C = 80°C				56	A
P _{tot}	total power dissipation	T _C = 25°C				290	W
V _{CE(sat)}	collector emitter saturation voltage	I _C = 50A; V _{GE} = 15 V	T _{VJ} = 25°C T _{VJ} = 125°C		1.8 2.1	2.1	V V
V _{GE(th)}	gate emitter threshold voltage	I _C = 2mA; V _{GE} = V _{CE}	T _{VJ} = 25°C	5.4	5.9	6.5	V
I _{CES}	collector emitter leakage current	V _{CE} = V _{CES} ; V _{GE} = 0 V	T _{VJ} = 25°C T _{VJ} = 125°C			0.1	mA mA
I _{GES}	gate emitter leakage current	V _{GE} = ±20 V				500	nA
Q _{G(on)}	total gate charge	V _{CE} = 600 V; V _{GE} = 15 V; I _C = 50 A			190		nC
t _{d(on)}	turn-on delay time	inductive load T_{VJ} = 125°C V_{CE} = 600V; I_C = 50A V_{GE} = ±15 V; R_G= 15 Ω			70		ns
t _r	current rise time				40		ns
t _{d(off)}	turn-off delay time				250		ns
t _f	current fall time				100		ns
E _{on}	turn-on energy per pulse				4.5		mJ
E _{off}	turn-off energy per pulse				5.5		mJ
RBSOA	reverse bias safe operating area	V_{GE} = ±15 V; R_G= 15 Ω V_{CEmax} = 1200V	T _{VJ} = 125°C			150	A
I _{CM}							
SCSOA	short circuit safe operating area	V_{CEmax} = 900 V V_{CE} = 900V; V_{GE} = ±15 V R_G= 15 Ω; non-repetitive	T _{VJ} = 125°C		200	10	μs A
t _{sc}	short circuit duration						
I _{sc}	short circuit current						
R _{thJC}	thermal resistance junction to case					0.43	K/W
R _{thCH}	thermal resistance case to heatsink				0.10		K/W
Diode							
V _{RRM}	max. repetitive reverse voltage	T _{VJ} = 25°C				1200	V
I _{F25}	forward current	T _C = 25°C				85	A
I _{F80}		T _C = 80°C				51	A
V _F	forward voltage	I _F = 60A	T _{VJ} = 25°C T _{VJ} = 125°C		1.95	2.20	V V
I _R	reverse current	V _R = V _{RRM}	T _{VJ} = 25°C T _{VJ} = 125°C			*	mA mA
* not applicable, see Ices value above					*		
Q _{rr}	reverse recovery charge	V_R= 600 V -di_F/dt = E+03 A/μs I_F = 60A; V_{GE} = 0 V	T _{VJ} = 125°C		8		μC
I _{RM}	max. reverse recovery current				60		A
t _{rr}	reverse recovery time				350		ns
E _{rec}	reverse recovery energy				2.5		mJ
R _{thJC}	thermal resistance junction to case					0.6	K/W
R _{thCH}	thermal resistance case to heatsink				0.10		K/W

Package SOT-227B (minibloc)				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal ¹⁾				150	A
T_{VJ}	virtual junction temperature			-40		150	°C
T_{op}	operation temperature			-40		125	°C
T_{stg}	storage temperature			-40		150	°C
Weight					30		g
M_D	mounting torque			1.1		1.5	Nm
M_T	terminal torque			1.1		1.5	Nm
$d_{Spp/App}$	creepage distance on surface striking distance through air	terminal to terminal	10.5	3.2			mm
$d_{Spb/Apb}$		terminal to backside	8.6	6.8			mm
V_{ISOL}	isolation voltage	t = 1 second	50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA	3000			V
		t = 1 minute		2500			V

¹⁾ I_{RMS} is typically limited by the pin-to-chip resistance (1); or by the current capability of the chip (2). In case of (1) and a product with multiple pins for one chip-potential, the current capability can be increased by connecting the pins as one contact.



Part number

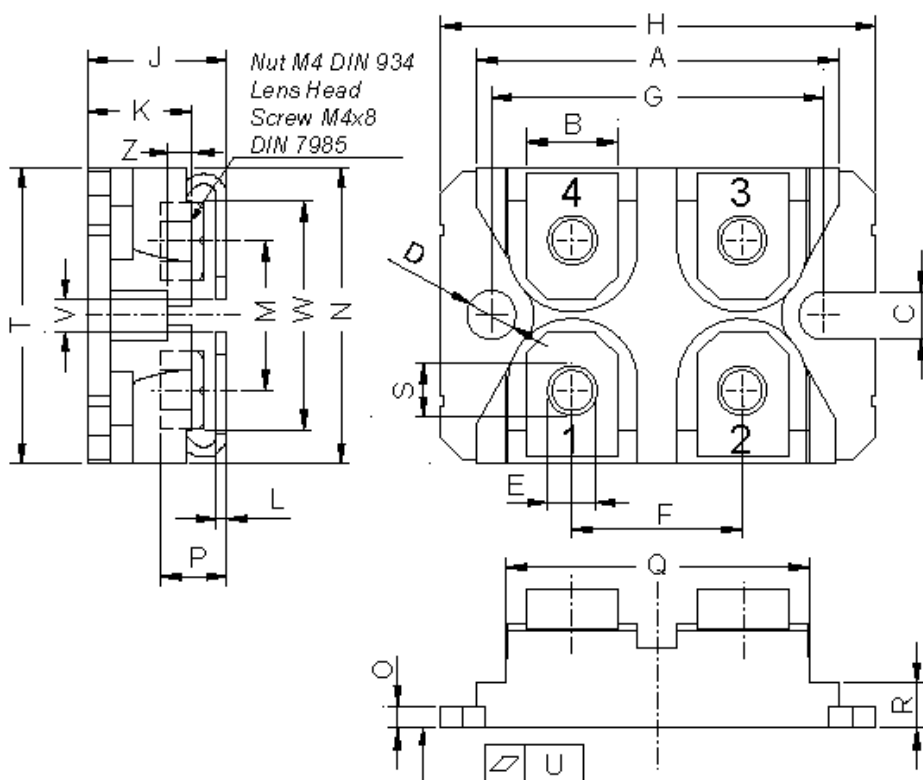
I = IGBT
X = XPT IGBT
A = Gen 1 / std
60 = Current Rating [A]
IF = Copack
1200 = Reverse Voltage [V]
NA = SOT-227B (minibloc)

Ordering	Part Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	IXA60IF1200NA	IXA60IF1200NA	Tube	10	508765

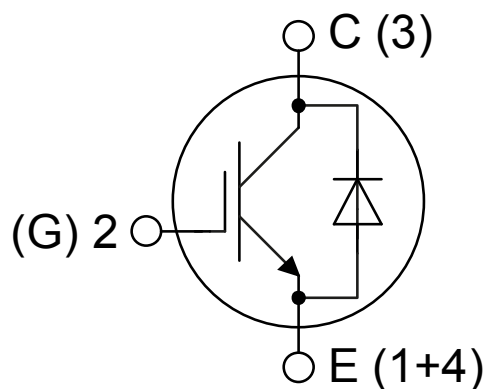
Similar Part	Package	Voltage class
IXA70I1200NA	SOT-227B (minibloc)	1200

Equivalent Circuits for Simulation		* on die level		$T_{VJ} = 150$ °C	
	V_0	IGBT	Diode		
	$V_{0\ max}$	1.1	1.25	V	
	$R_{0\ max}$	28	14.2	mΩ	

Outlines SOT-227B (minibloc)



Dim.	Millimeter		Inches	
	min	max	min	max
A	31.50	31.88	1.240	1.255
B	7.80	8.20	0.307	0.323
C	4.09	4.29	0.161	0.169
D	4.09	4.29	0.161	0.169
E	4.09	4.29	0.161	0.169
F	14.91	15.11	0.587	0.595
G	30.12	30.30	1.186	1.193
H	37.80	38.23	1.488	1.505
J	11.68	12.22	0.460	0.481
K	8.92	9.60	0.351	0.378
L	0.74	0.84	0.029	0.033
M	12.50	13.10	0.492	0.516
N	25.15	25.42	0.990	1.001
O	1.95	2.13	0.077	0.084
P	4.95	6.20	0.195	0.244
Q	26.54	26.90	1.045	1.059
R	3.94	4.42	0.155	0.167
S	4.55	4.85	0.179	0.191
T	24.59	25.25	0.968	0.994
U	-0.05	0.10	-0.002	0.004
V	3.20	5.50	0.126	0.217
W	19.81	21.08	0.780	0.830
Z	2.50	2.70	0.098	0.106



IGBT

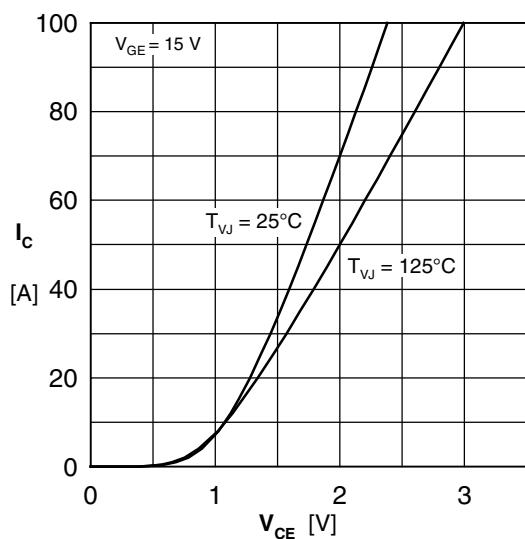


Fig. 1 Typ. output characteristics

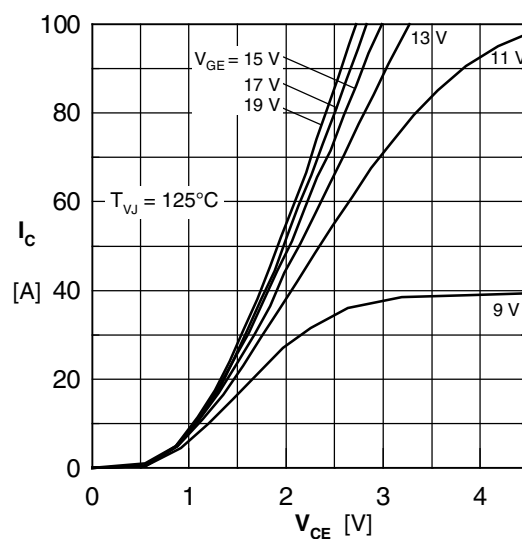


Fig. 2 Typ. output characteristics

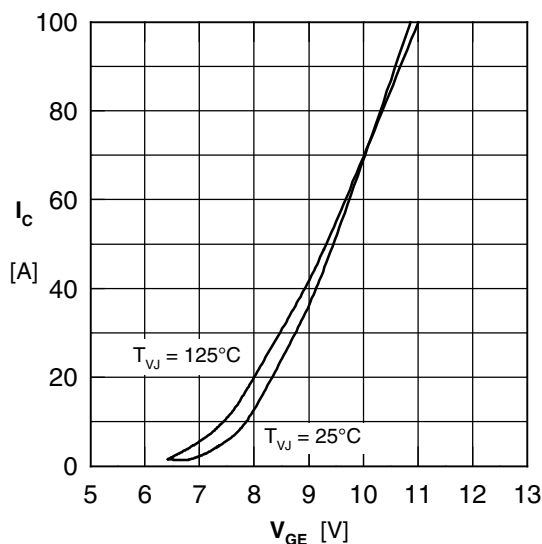


Fig. 3 Typ. transfer characteristics

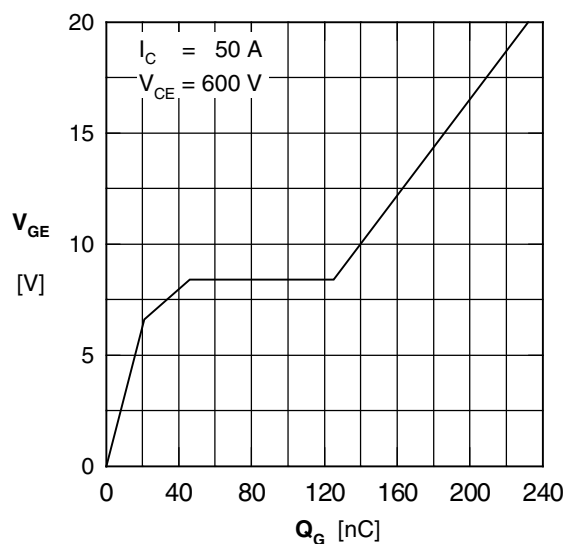


Fig. 4 Typ. turn-on gate charge

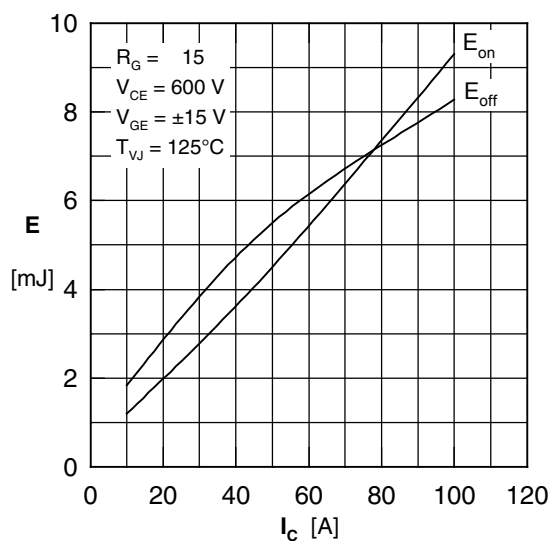


Fig. 5 Typ. switching energy vs. collector current

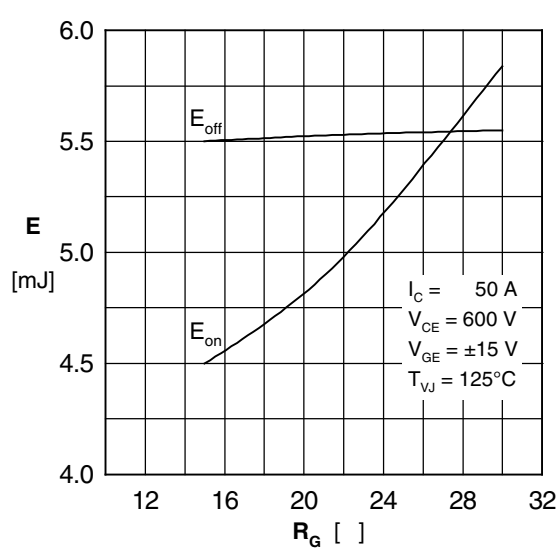


Fig. 6 Typ. switching energy vs. gate resistance

Diode

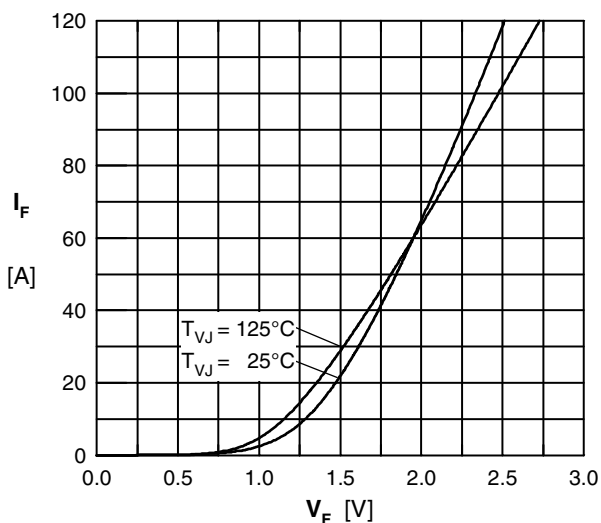


Fig. 7 Typ. Forward current versus V_F

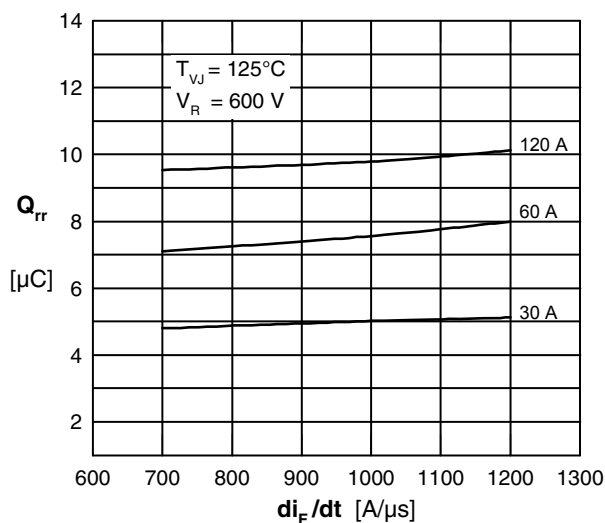


Fig. 8 Typ. reverse recov.charge Q_{rr} vs. di/dt

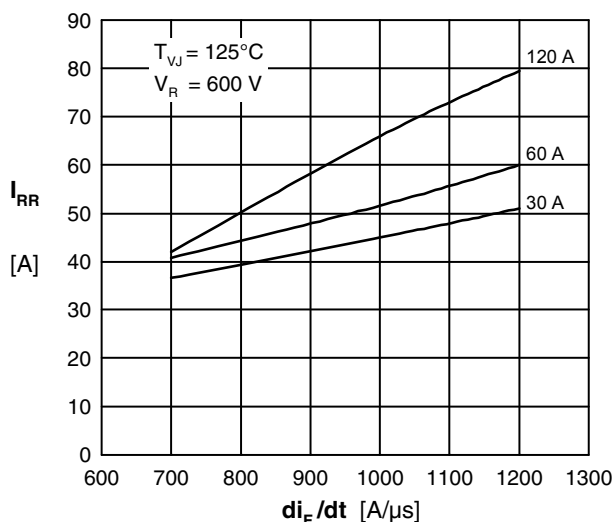


Fig. 9 Typ. peak reverse current I_{RM} vs. di/dt

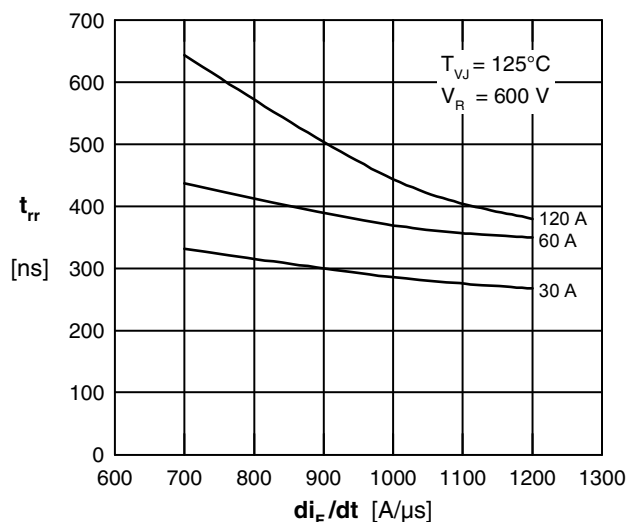


Fig. 10 Typ. recovery time t_{rr} versus di/dt

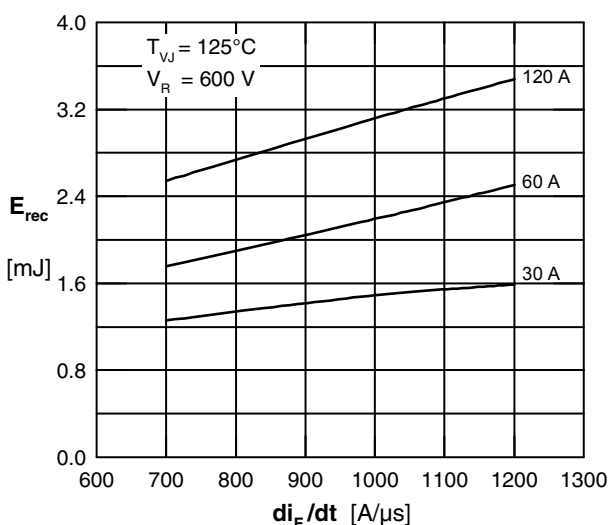


Fig. 11 Typ. recovery energy E_{rec} versus di/dt

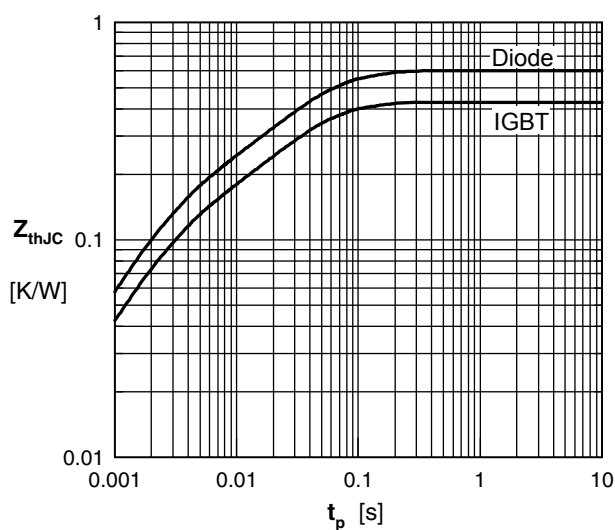


Fig. 12 Typ. transient thermal impedance